

4.3G Analog InGaAs PIN Module

Features

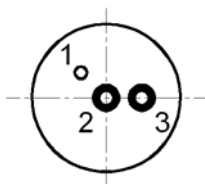
Low Dark Current
High Responsivity
Excellent Reliability
High Linearity

Applications

WCDMA/GSM/CDMA/ PHS
CATV



PIN assignment



pin	Function
1(case)	GND
2	N
3	P

This device is susceptible to damage as a result of electrostatic discharge (ESD). A static free environment is highly recommended. Follow guidelines according to proper ESD procedures



Absolute maximum ratings

Parameter	Symbol	Value	Unit
Storage temperature	T _{st}	-40~+85	°C
Operating temperature	T _{op}	-40~+85	°C
Reverse voltage	V _R	30	V
Soldering temperature/time	—	260/10	°C/ s

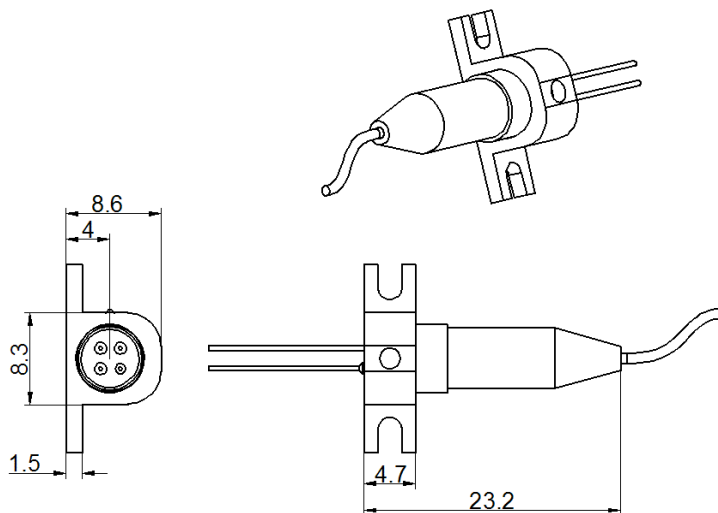
Optical & electrical characteristics(T=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Detection range	λ	1100	-	1650	nm	-
Dark current	I _d	-	0.2	1	nA	V _R =5V
Quantum efficiency	R	0.80	0.85	-	A/W	V _R =5V,1310 nm
Band width	BW	4	4.5	-	GHz	R _L =50Ω/-3dB
Capacitance	C _t	-	0.2	0.35	pF	V _R =5V
2nd Order Intermodulation	CSO	-	-	-70	dBc	Note 1
3rd Order Inter-Modulation	CTB	-	-	-85	dBc	Note 1
Return Loss	RL	-40	-	-	dB	

Note 1:f1=400MHz, P1=-3dBm; f2=450.25MHz, P2=-3dBm;

I=40%.Pavg=0dBm.Rload=50 Ω IMD2:f1+f2=850.25MHz.VR=12V

Dimensions Diagram



Order information

SPA	X	X	X	X
	type 1:InGaAs	Band width 1:1.25G 2:2.5G 4:4.3G	Package 1:a 2:b S,spec.	Connect 1,SC/APC 2,FC/APC

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